

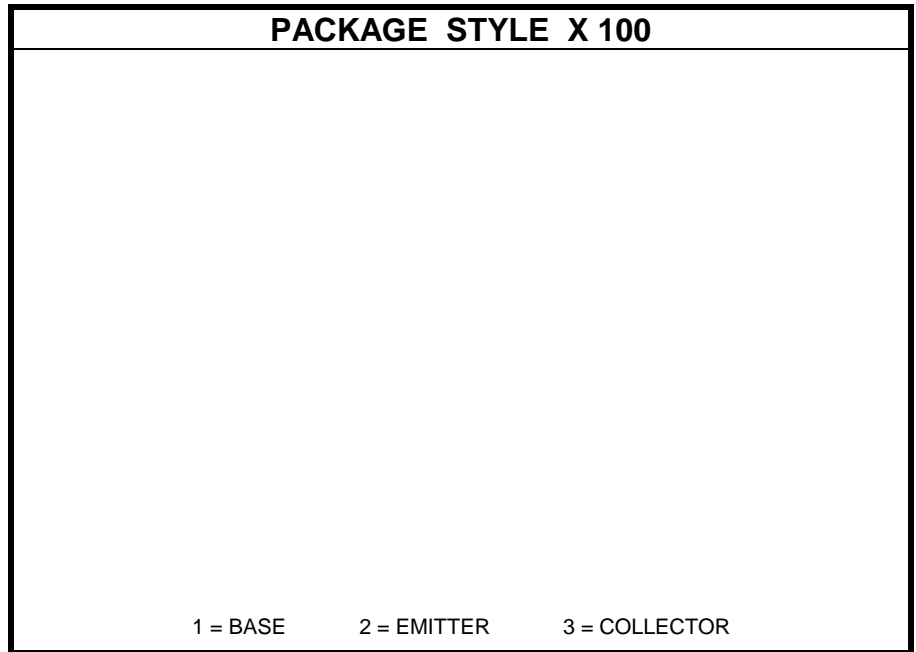
SILICON NPN RF TRANSISTOR

DESCRIPTION:

The **ASI BFQ34T** is Designed for General Purpose Wideband Amplifier and Oscillator Applications.

MAXIMUM RATINGS

I_C	150 mA
V_{CE}	15 V
P_{DISS}	1.0 W @ $T_A = 45^\circ\text{C}$
T_J	-65°C to $+175^\circ\text{C}$
T_{STG}	-65°C to $+150^\circ\text{C}$

PACKAGE STYLE X 100		
		
1 = BASE	2 = EMITTER	3 = COLLECTOR

CHARACTERISTICS $T_C = 25^\circ\text{C}$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	$I_C = 10\text{ mA}$	15	18		V
BV_{CBO}	$I_C = 1.0\text{ mA}$	25	30		V
I_{CBO}	$V_{CB} = 15\text{ V}$			100	μA
BV_{EBO}	$I_E = 100\ \mu\text{A}$	2.0	2.6		V
h_{FE}	$V_{CE} = 10\text{ V}$ $I_C = 100\text{ mA}$	30	100	250	---
C_c	$V_{CB} = 10\text{ V}$ $f = 1.0\text{ MHz}$		2.0		pF
C_e	$V_{CB} = 0.5\text{ V}$ $f = 1.0\text{ MHz}$		10		pF
C_{re}	$V_{CB} = 10\text{ V}$ $f = 1.0\text{ MHz}$		1.2		pF
f_t	$V_{CE} = 10\text{ V}$ $I_C = 10\text{ mA}$ $f = 500\text{ MHz}$		3.7		GHz